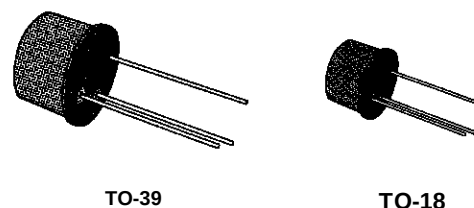


HIGH-SPEED SWITCHES

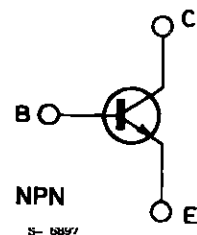
DESCRIPTION

The 2N2218, 2N2219, 2N2221 and 2N2222 are silicon planar epitaxial NPN transistors in Jedec TO-39 (for 2N2218 and 2N2219) and in Jedec TO-18 (for 2N2221 and 2N2222) metal cases. They are designed for high-speed switching applications at collector currents up to 500 mA, and feature useful current gain over a wide range of collector current, low leakage currents and low saturation voltages.

 2N2218/2N2219 approved to CECC 50002-100, 2N2221/2N2222 approved to CECC 50002-101 available on request.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	60	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	30	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	5	V
I_C	Collector Current	0.8	A
P_{tot}	Total Power Dissipation at $T_{amb} \leq 25^\circ\text{C}$ for 2N2218 and 2N2219	0.8	W
	for 2N2221 and 2N2222	0.5	W
	at $T_{case} \leq 25^\circ\text{C}$ for 2N2218 and 2N2219	3	W
	for 2N2221 and 2N2222	1.8	W
T_{stg}	Storage Temperature	- 65 to 200	$^\circ\text{C}$
T_j	Junction Temperature	175	$^\circ\text{C}$

2N2218-2N2219-2N2221-2N2222

THERMAL DATA

			2N2218 2N2219	2N2221 2N2222
$R_{th\ j-case}$	Thermal Resistance Junction-case	Max	50 °C/W	83.3 °C/W
$R_{th\ j-amb}$	Thermal Resistance Junction-ambient	Max	187.5 °C/W	300 °C/W

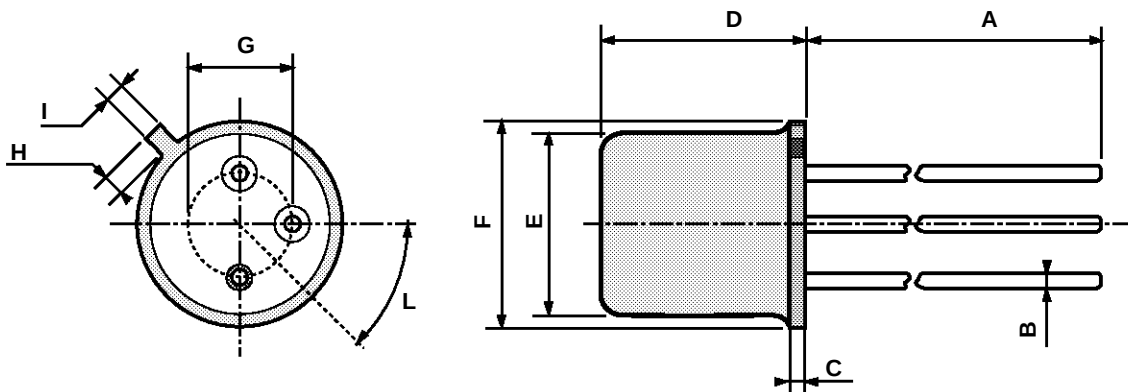
ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ °C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cutoff Current ($I_E = 0$)	$V_{CB} = 50\text{ V}$ $V_{CB} = 50\text{ V}$ $T_{amb} = 150\text{ °C}$			10 10	nA μA
I_{EBO}	Emitter Cutoff Current ($I_C = 0$)	$V_{EB} = 3\text{ V}$			10	nA
$V_{(BR)\ CBO}$	Collector-base Breakdown Voltage ($I_E = 0$)	$I_C = 10\text{ }\mu\text{A}$	60			V
$V_{(BR)CEO}^*$	Collector-emitter Breakdown Voltage ($I_B = 0$)	$I_C = 10\text{ mA}$	30			V
$V_{(BR)\ EBO}$	Emitter-base Breakdown Voltage ($I_C = 0$)	$I_E = 10\text{ }\mu\text{A}$	5			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 150\text{ mA}$ $I_B = 15\text{ mA}$ $I_C = 500\text{ mA}$ $I_B = 50\text{ mA}$			0.4 1.6	V V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = 150\text{ mA}$ $I_B = 15\text{ mA}$ $I_C = 500\text{ mA}$ $I_B = 50\text{ mA}$			1.3 2.6	V V
h_{FE}^*	DC Current Gain	for 2N2218 and 2N2221 $I_C = 0.1\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 1\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}$ $V_{CE} = 1\text{ V}$ for 2N2219 and 2N2222 $I_C = 0.1\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 1\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}$ $V_{CE} = 1\text{ V}$	20 25 35 40 20 20 35 50 75 100 30 50		120 300	
f_T	Transition Frequency	$I_C = 20\text{ mA}$ $V_{CE} = 20\text{ V}$ $f = 100\text{ MHz}$	250			MHz
C_{CBO}	Collector-base Capacitance	$I_E = 0$ $f = 100\text{ kHz}$ $V_{CB} = 10\text{ V}$			8	pF
$R_{e(hie)}$	Real Part of Input Impedance	$I_C = 20\text{ mA}$ $V_{CE} = 20\text{ V}$ $f = 300\text{ MHz}$			60	Ω

* Pulsed : pulse duration = 300 μs , duty cycle = 1 %.

TO-18 MECHANICAL DATA

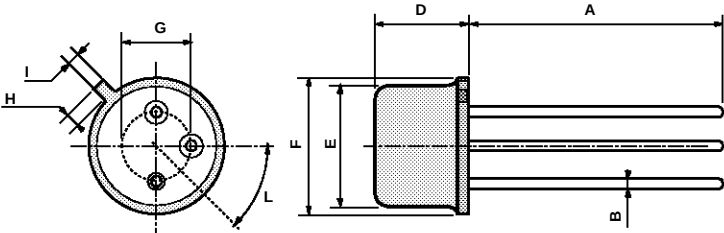
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		12.7			0.500	
B			0.49			0.019
D			5.3			0.208
E			4.9			0.193
F			5.8			0.228
G	2.54			0.100		
H			1.2			0.047
I			1.16			0.045
L	45°			45°		



0016043

TO39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



P008B

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A